

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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WeEn Semiconductors



BTA316X-800B0



3Q Hi-Com Triac

Rev. 2 — 17 November 2011

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B0" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- High immunity to false turn-on by dV/dt
- High minimum I_{GT} for guaranteed immunity to gate noise
- High voltage capability
- Isolated mounting base package
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high commutation capability with maximum false trigger immunity

1.3 Applications

- Electronic thermostats
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids
- Refrigeration and air conditioning compressors



1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 ms$; see Figure 4; see Figure 5	-	-	140	Α
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 45 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	16	Α
Static cha	nracteristics					
I _{GT} gate trigger current	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+G+; T_j = 25 \text{ °C;}$ see Figure 7	10	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-; } T_j = 25 \text{ °C; }$ see Figure 7	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-}; T_j = 25 ^{\circ}\text{C};$ see Figure 7	10	-	50	mA

2. Pinning information

Table 2. Pinning information

		, miormanon		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N .
2	T2	main terminal 2	mb	T2—T1
3	G	gate		`G sym051
mb	n.c.	mounting base; isolated		
			U U U 1 2 3	

SOT186A (TO-220F)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA316X-800B0	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 45$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	16	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	140	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	150	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	98	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 20 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

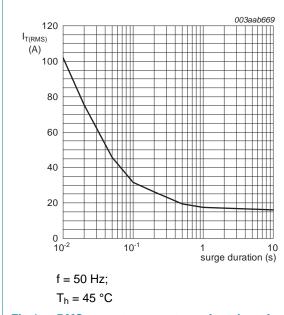


Fig 1. RMS on-state current as a function of surge duration; maximum values

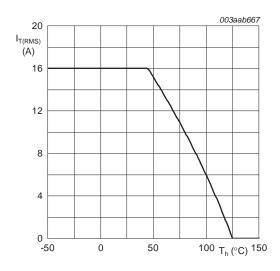


Fig 2. RMS on-state current as a function of heatsink temperature; maximum values

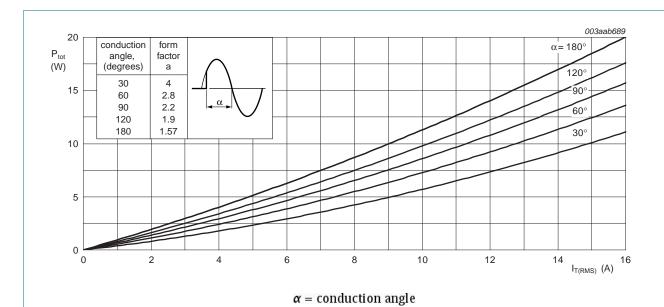


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

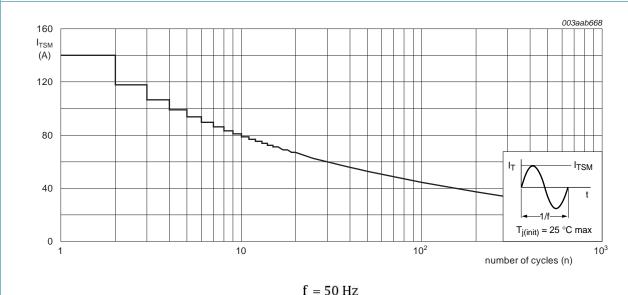
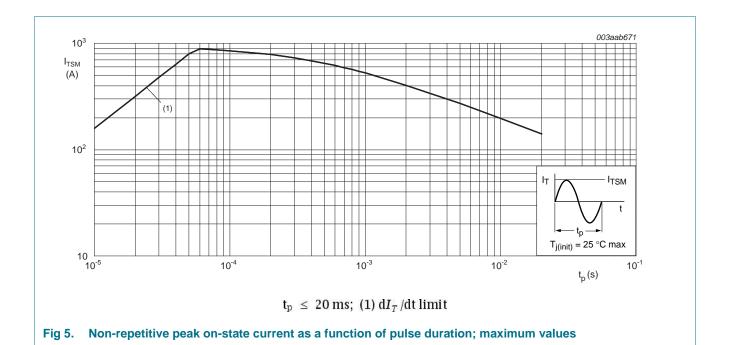


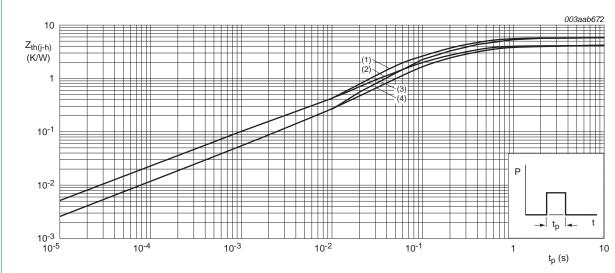
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see Figure 6	-	-	4	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

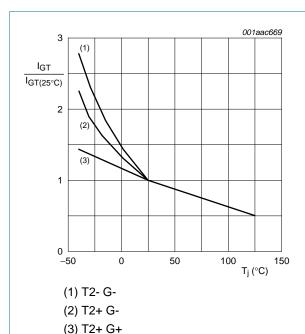
Table 6. Isolation characteristics

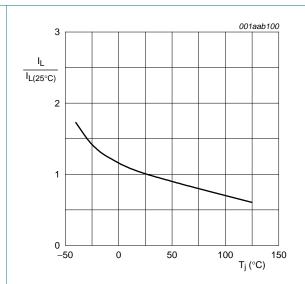
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all three terminals to external heatsink; sinusoidal waveform; clean and dust free ; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1 \text{ MHz}$; $T_h = 25 ^{\circ}\text{C}$	-	10	-	pF

7. Characteristics

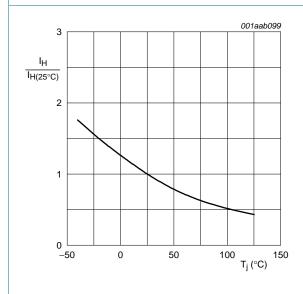
Table 7. Characteristics

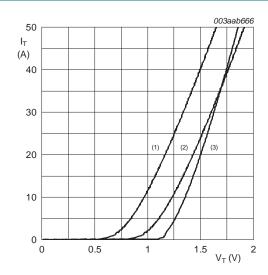
Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+; T_j = 25 \text{ °C;}$ see <u>Figure 7</u>	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 °C;$ see Figure 7	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-}; T_j = 25 \text{ °C};$ see Figure 7	10	-	50	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	60	mA
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	90	mA	
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-}; T_j = 25 \text{ °C};$ see Figure 8	-	-	60	mA	
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ J}}$	-	-	60	mΑ
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; see <u>Figure 10</u>	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	0.8	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; exponential waveform; gate open circuit	2500	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s}; (snubberless condition); gate open circuit$	20	-	-	A/ms





- Fig 7. Normalized gate trigger current as a function of junction temperature
- Fig 8. Normalized latching current as a function of junction temperature





 $V_0 = 1.024 \text{ V}$

 $R_s = 0.021 \Omega$

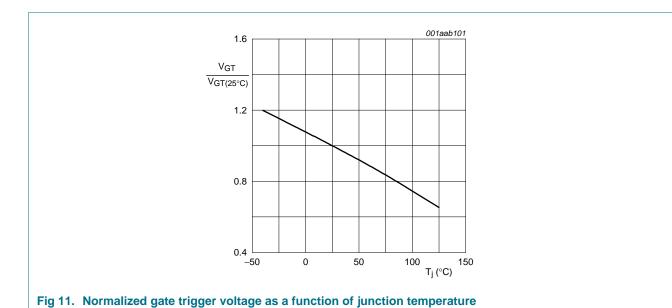
(1) T_j = 125 °C; typical values

(2) $T_j = 125$ °C; maximum values

(3) T_j = 25 °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature

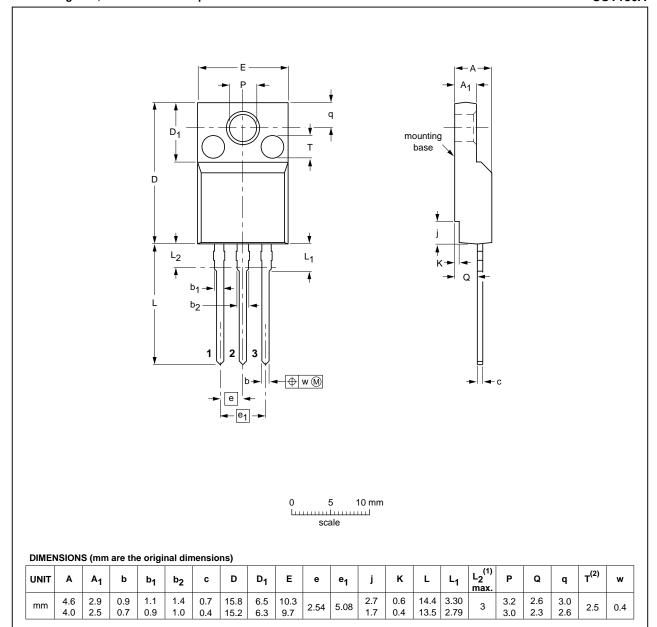
Fig 10. On-state current as a function of on-state voltage



8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

			EUROPEAN	ISSUE DATE
IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
	3-lead TO-220F			-02-04-09 06-02-14
_	IEC			IEC JEDEC JEHA

Fig 12. Package outline SOT186A (TO-220F)

BTA316X-800B0

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA316X-800B0 v.2	20111117	Product data sheet	-	BTA316X-800B0 v.1
Modifications:	 Various changes 	s to content.		
BTA316X-800B0 v.1	20101112	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data2
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics6
6	Isolation characteristics
7	Characteristics7
8	Package outline10
9	Revision history11
10	Legal information12
10.1	Data sheet status
10.2	Definitions
10.3	Disclaimers
10.4	Trademarks13
11	Contact information 13

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